

ABSTRACT OF THE DISCLOSURE

The present invention discloses a method for forming a bit line of a semiconductor device which can easily perform a contact process of the semiconductor device, by forming parallel rows of I-shaped active regions, a plug poly and a ladder-type bit line. The spacing between adjacent active regions is maintained at the minimum line width. Two word lines of minimum line width and separated by the minimum line width are formed on the active region. The word lines are perpendicular to the active regions. A plug poly is formed on the active region between the word lines. A bit line contact plug is formed over the plug poly and a device isolation region. A bit line of minimum line width contacts the bit line contact plug and aligned generally parallel to the word lines is formed in a ladder-type configuration. That is, one side the lower portion of the contact plug contacts the plug poly, and the upper portion of the other side of the contact plug contacts the bit line. As a result, a storage electrode contact process may be performed using a self aligned method.